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Vishay Siliconix

Automotive P-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	-30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0085				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0200				
I _D (A)	-22				
Configuration	Single				

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified c
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

G S
D
P-Channel MOSFET

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	SQ4483EY (for detailed order number please see www.vishay.com/doc?79771)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	-30	\/	
Gate-source voltage	V _{GS}	± 20	V	
Continuous drain current	I _D	-30		
Continuous drain current		-30		
Continuous source current (diode conduction)	I _S	-30	Α	
Pulsed drain current ^a	I _{DM}	-84		
Single pulse avalanche current	I _{AS}	-32		
Single pulse avalanche energy	E _{AS}	51	mJ	
Maximum power dissipation ^a	D	7	W	
iviaximum power dissipation 4	P_{D}	2	VV	
Operating junction and storage temperature range	T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount b	R_{thJA}	85	°C/W		
Junction-to-case (drain)		R _{thJF}	21	C/VV		

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. Parametric verification ongoing



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static		-			•		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-30	-	-	.,
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-2.0	-2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = -30 V	=	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -30 V, T _J = 125 °C	-	-	-50	μΑ
		V _{GS} = 0 V	V _{DS} = -30 V, T _J = 175 °C	-	-	-150	1
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 \text{ V}$	-30	-	-	Α
		V _{GS} = -10 V	I _D = -10 A	-	0.0070	0.0085	Ω
Drain-source on-state resistance ^a	D	$V_{GS} = -10 \text{ V}$	I _D = -10 A, T _J = 125 °C	ì	-	0.0130	
Diditi-Source off-State resistance	R _{DS(on)}	$V_{GS} = -10 \text{ V}$	I _D = -10 A, T _J = 175 °C	1	-	0.0150	
		$V_{GS} = -4.5 \text{ V}$	$I_D = -7 A$	ì	0.0160	0.0200	
Forward transconductance b	9 _{fs}	V _{DS} = -10 V, I _D = -10 A		1	32	ı	S
Dynamic ^b							
Input capacitance	C _{iss}			-	3400	4500	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = -15 \text{ V}, f = 1 \text{ MHz}$	-	712	890	pF
Reverse transfer capacitance	C _{rss}			-	580	770	
Total gate charge ^c	Qg			1	75	113	
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -15 \text{ V}, I_{D} = -10 \text{ A}$	1	9.5	-	nC
Gate-drain charge ^c	Q _{gd}			-	19	-	
Gate resistance	R _g	f = 1 MHz		1	2	3	Ω
Turn-on delay time ^c	t _{d(on)}			=	20	25	
Rise time ^c	t _r	V_{DD} = -15 V, R_L = 1.5 Ω $I_D \cong$ -10 A, V_{GEN} = -10 V, R_g = 1 Ω		1	146	189	ns
Turn-off delay time ^c	t _{d(off)}			-	57	75	
Fall time ^c	t _f			ı	20	25	
Source-Drain Diode Ratings and Char	acteristics ^b						
Pulsed current ^a	I _{SM}			-	-	-84	Α

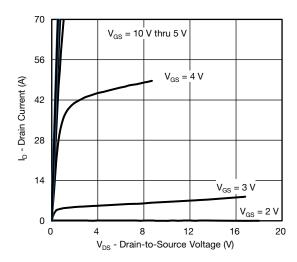
Notes

- d. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- e. Guaranteed by design, not subject to production testing
- f. Independent of operating temperature

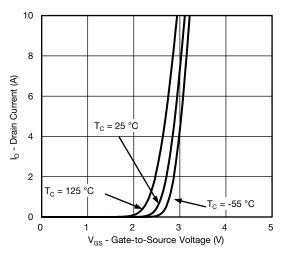
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



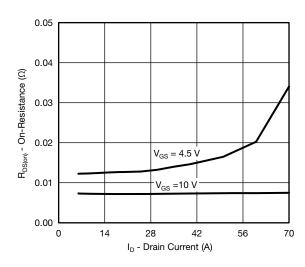
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



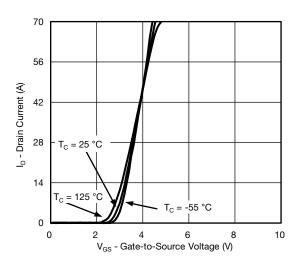
Output Characteristics



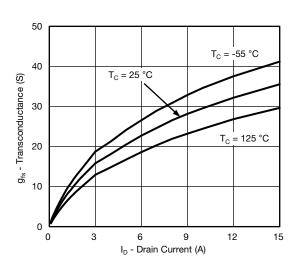
Transfer Characteristics



On-Resistance vs. Drain Current



Transfer Characteristics



Transconductance





0 L

5

6000 5000 5000 C_{iss} 1000 C_{rss}

Capacitance

15

 $V_{\rm DS}$ - Drain-to-Source Voltage (V)

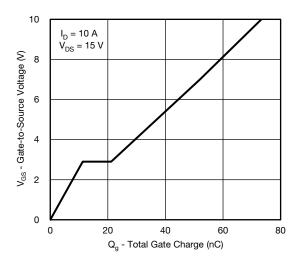
20

25

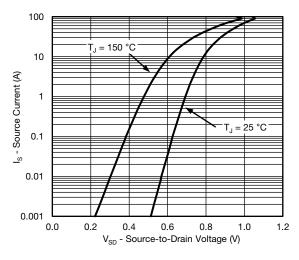
30



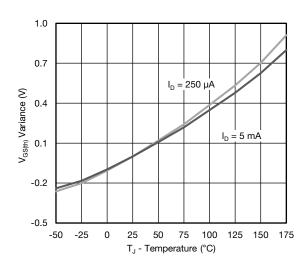
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



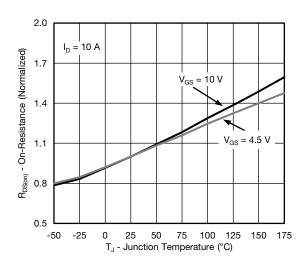
Gate Charge



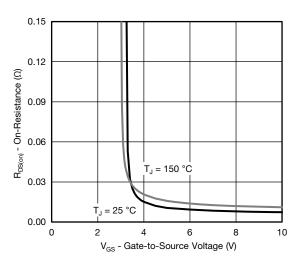
Source Drain Diode Forward Voltage



Threshold Voltage

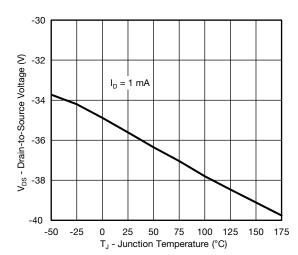


On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

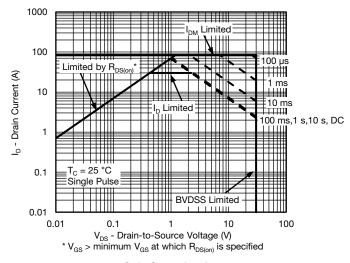




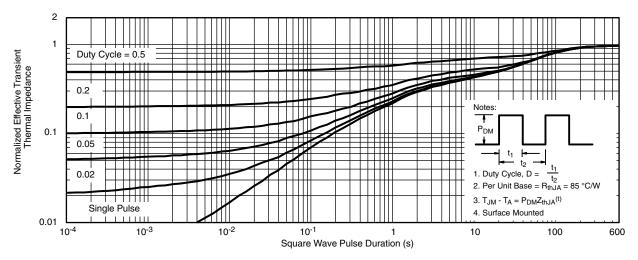
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



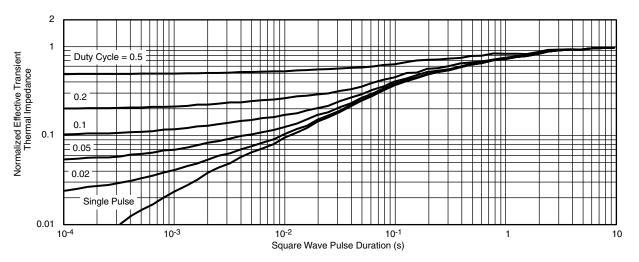
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS		INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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